

Features

- Low On-Resistance
- Low Gate Threshold Voltage $V_{GS(th)} < 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- **Lead Free/RoHS Compliant (Note 2)**
- **ESD Protected Gate**
- **"Green" Device (Note 3)**

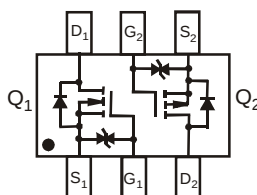
Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 7
- Ordering & Date Code Information: See Page 7
- Weight: 0.006 grams (approximate)



TOP VIEW

SOT-363


 TOP VIEW
 Internal Schematic

Maximum Ratings N-CHANNEL – Q₁ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±8	V
Drain Current (Note 1)	I_D	$T_A = 25^\circ C$ $T_A = 85^\circ C$ 540 390	mA

Maximum Ratings P-CHANNEL – Q₂ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	±8	V
Drain Current (Note 1)	I_D	$T_A = 25^\circ C$ $T_A = 85^\circ C$ -430 -310	mA

Thermal Characteristics – Total Device @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P_d	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics N-CHANNEL – Q₁ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	± 1	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	0.5	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	0.4	0.55	Ω	V _{GS} = 4.5V, I _D = 540mA
		—	0.5	0.70		V _{GS} = 2.5V, I _D = 500mA
		—	0.7	0.90		V _{GS} = 1.8V, I _D = 350mA
Forward Transfer Admittance	Y _{fs}	200	—	—	mS	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage (Note 4)	V _{SD}	0.5	—	1.2	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	150	pF	V _{DS} = 16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	20	pF	

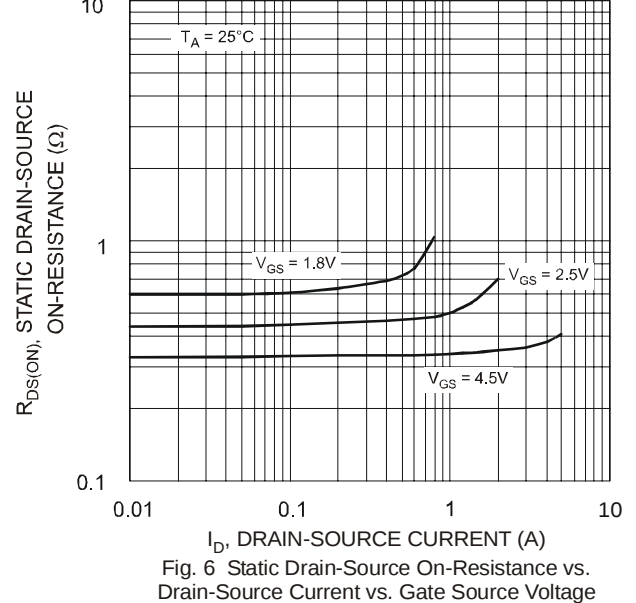
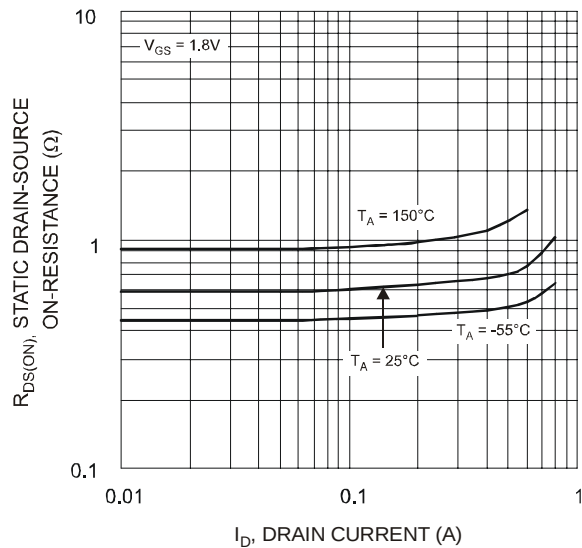
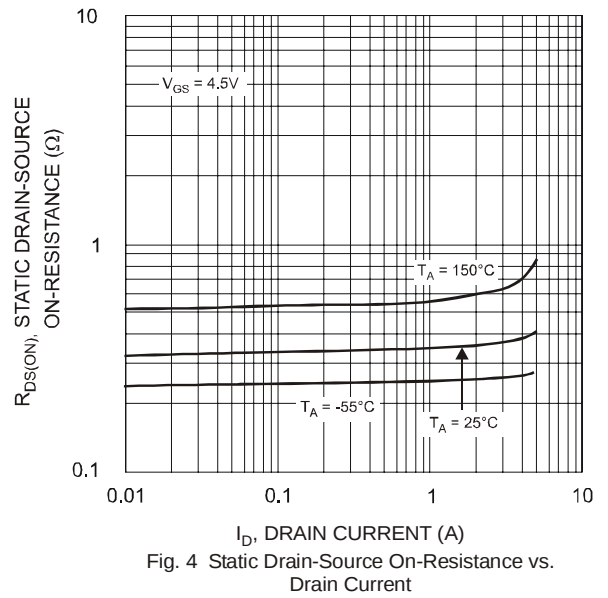
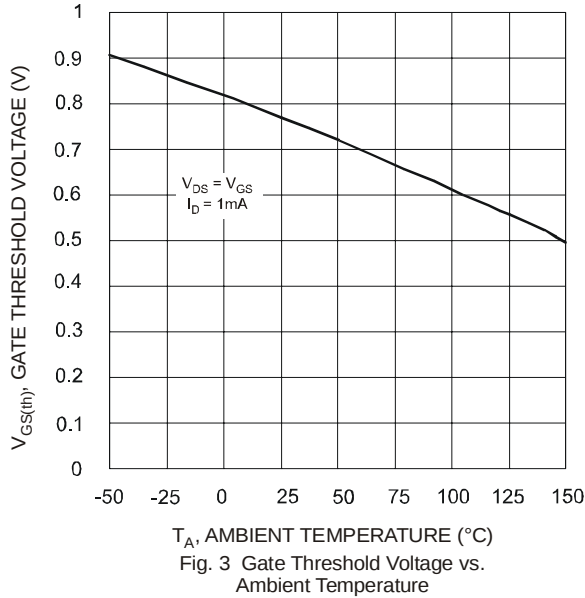
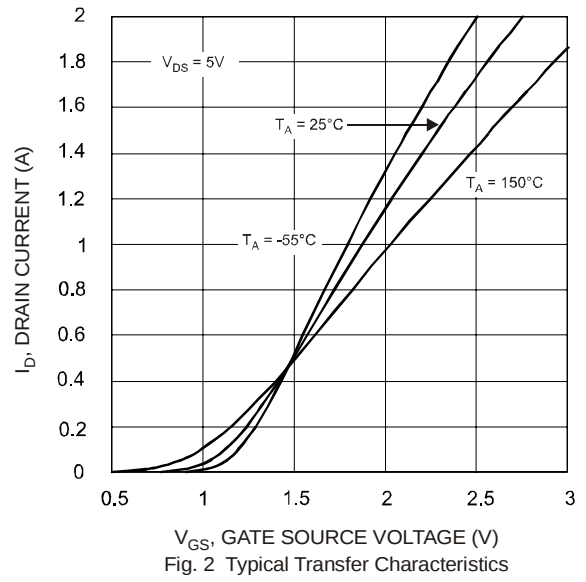
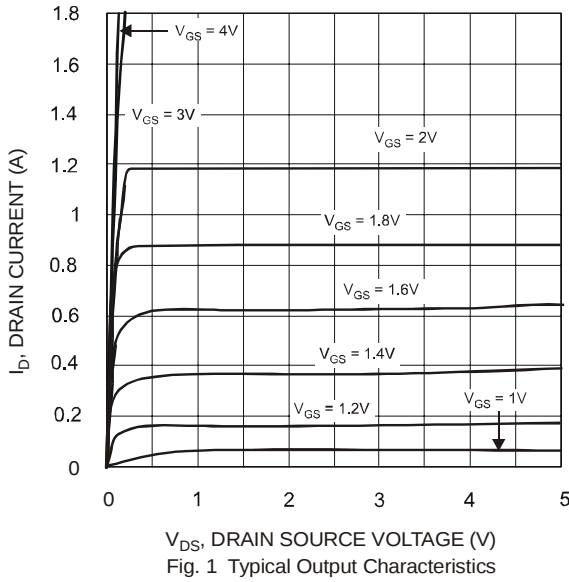
Electrical Characteristics P-CHANNEL – Q₂ @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	± 1.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	0.7	0.9	Ω	V _{GS} = -4.5V, I _D = -430mA
			1.1	1.4		V _{GS} = -2.5V, I _D = -300mA
			1.7	2.0		V _{GS} = -1.8V, I _D = -150mA
Forward Transfer Admittance	Y _{fs}	200	—	—	mS	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage (Note 4)	V _{SD}	-0.5	—	-1.2	V	V _{GS} = 0V, I _S = -115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	175	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	30	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	20	pF	

Notes: 4. Short duration pulse test used to minimize self-heating effect.

Q₁, N-CHANNEL

NEW PRODUCT



Q1, N-CHANNEL, continued

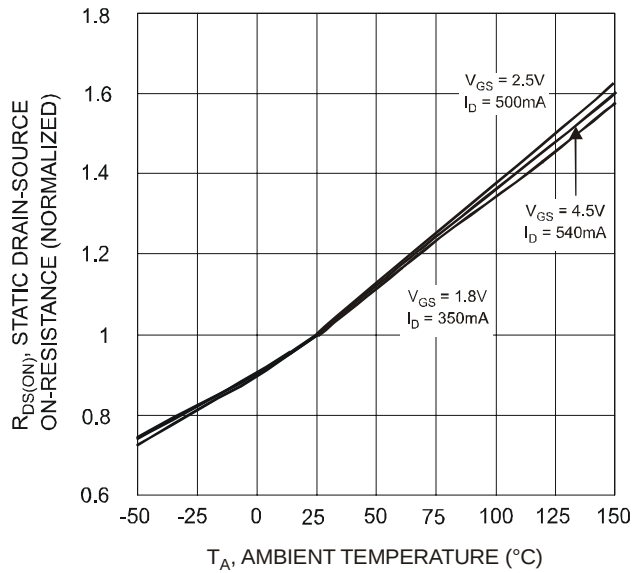


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

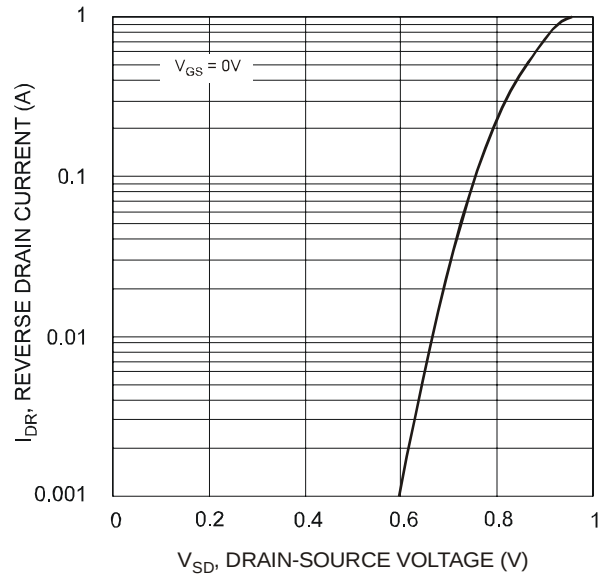


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

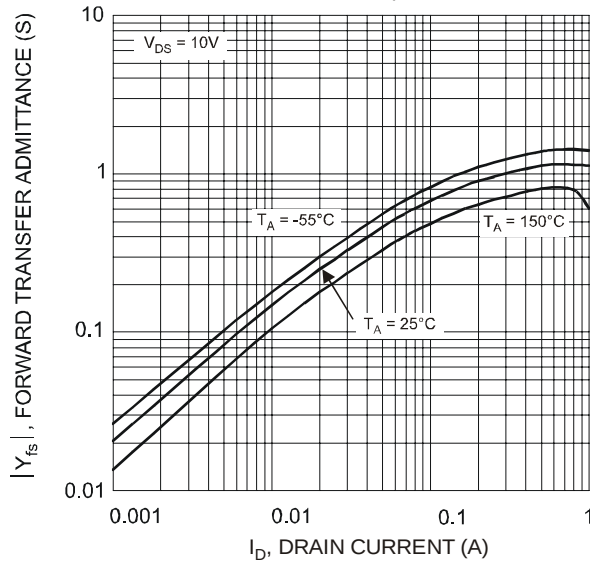


Fig. 9 Forward Transfer Admittance vs. Drain Current

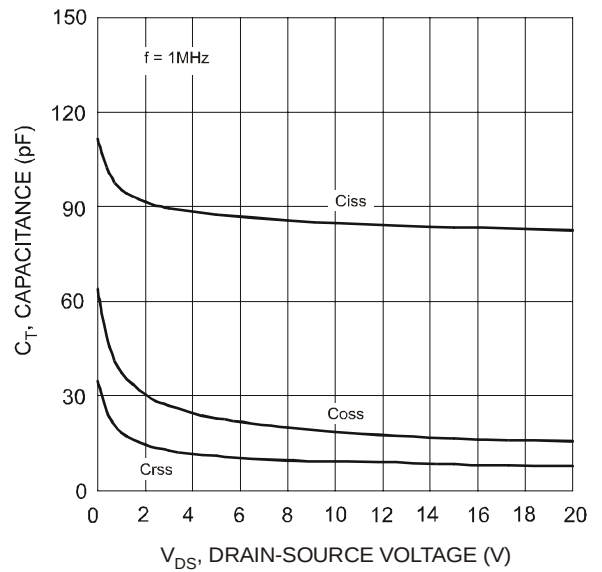
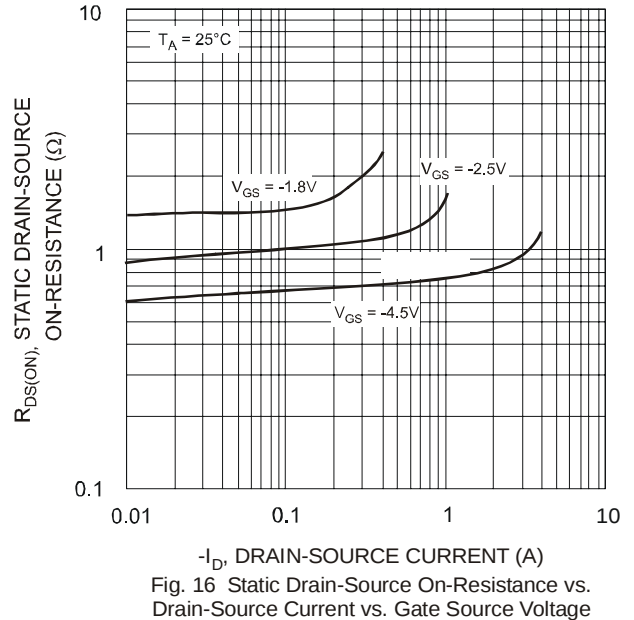
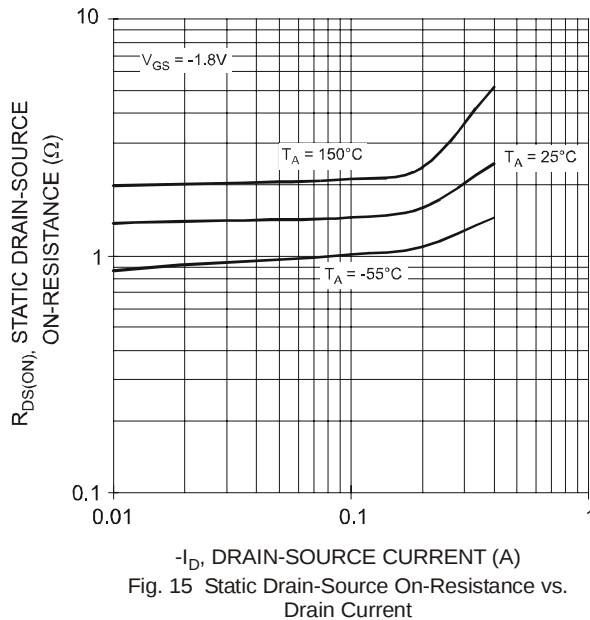
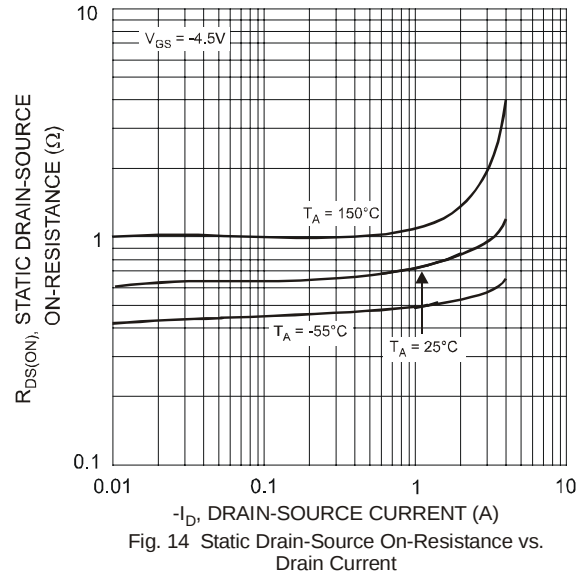
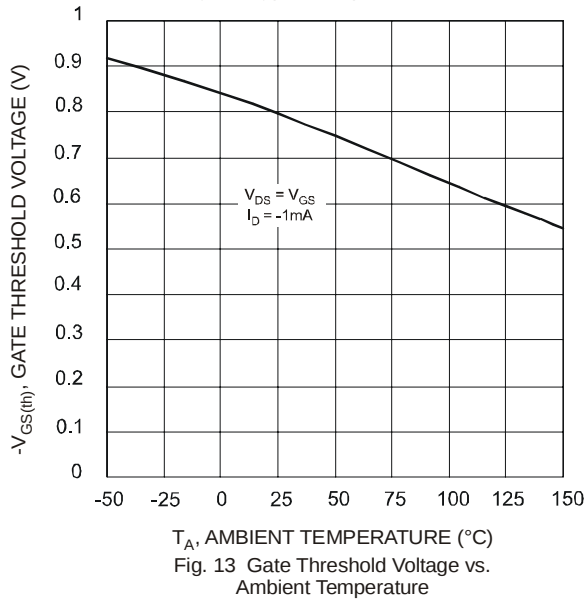
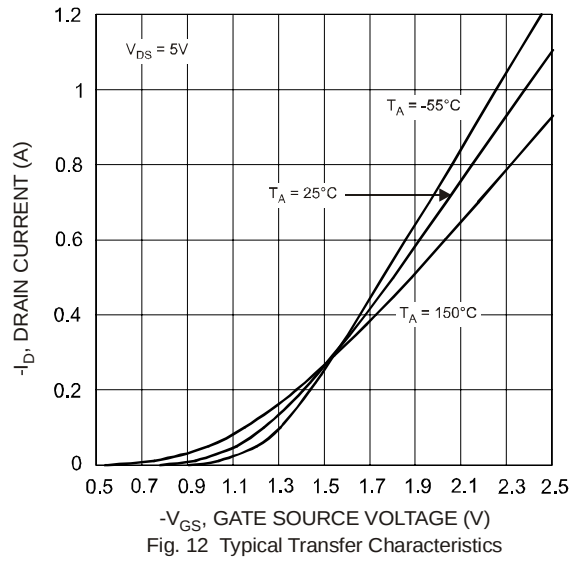
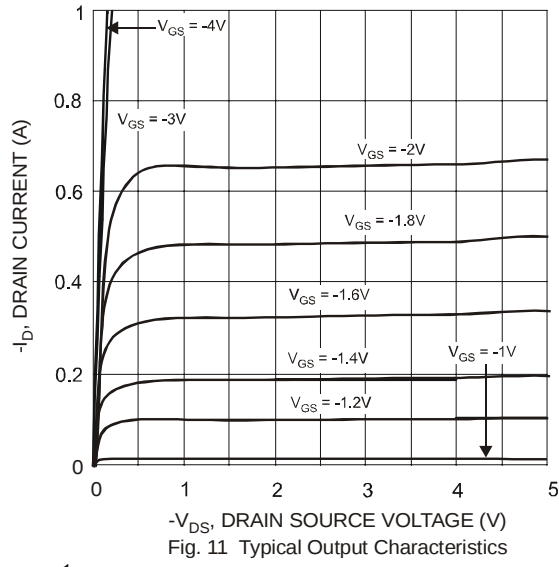


Fig. 10 Typical Capacitance

Q₂, P-CHANNEL

NEW PRODUCT



Q₂, P-CHANNEL, Continued

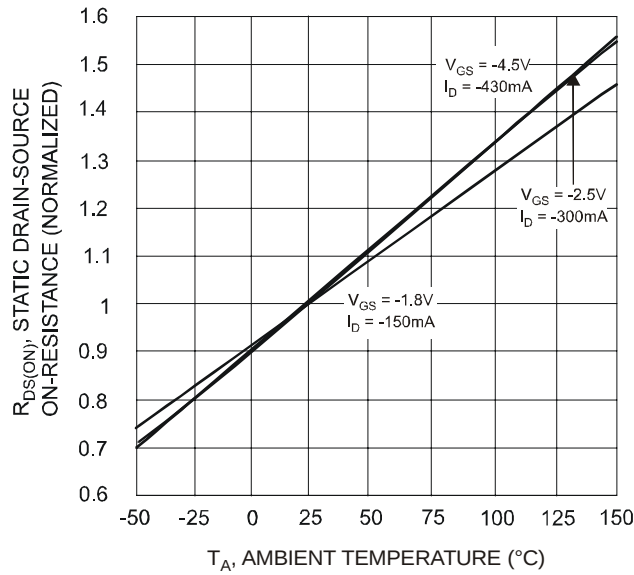


Fig. 17 Static Drain-Source On-State Resistance vs. Ambient Temperature

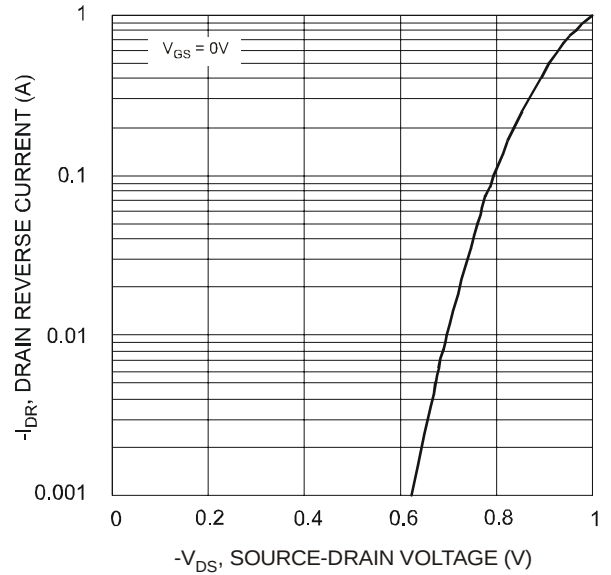


Fig. 18 Reverse Drain Current vs. Source-Drain Voltage

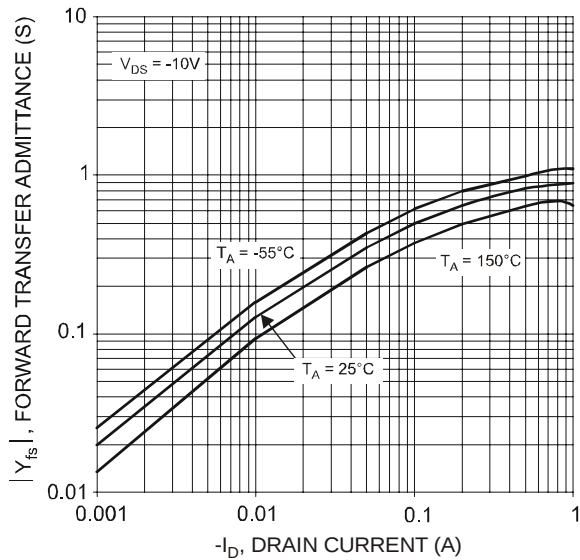


Fig. 19 Forward Transfer Admittance vs. Drain Current

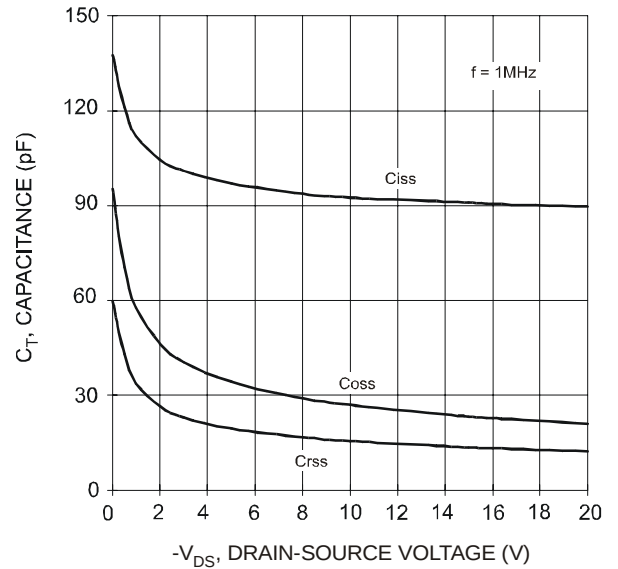
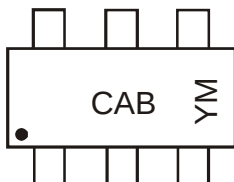


Fig. 20 Typical Capacitance

Ordering Information (Note 5)

Part Number	Case	Packaging
DMC2004DWK-7	SOT-363	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

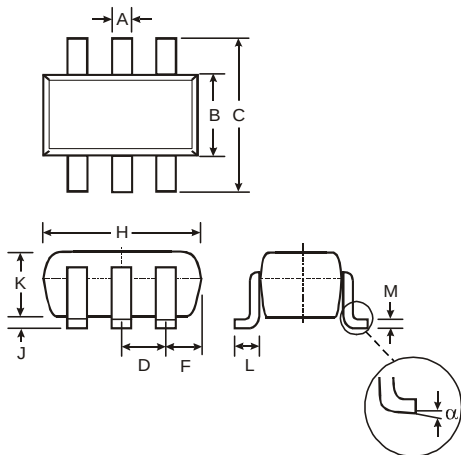
Marking Information


CAB = Marking Code
 YM = Date Code Marking
 Y = Year ex: U = 2007
 M = Month ex: 9 = September

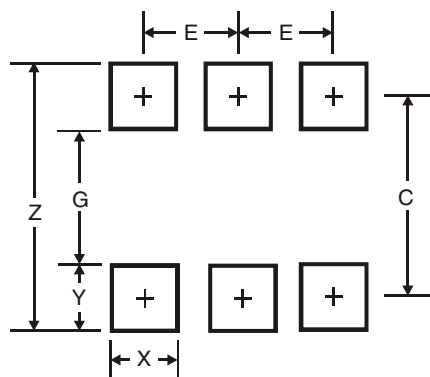
Date Code Key

Year	2007	2008	2009	2010	2011	2012
Code	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions


SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout


Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C	1.9
E	0.65

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